

YAO-3950

PATENT

Amdt
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yoshihisa Nagano et al. : Art Unit: 2815
Serial No.: 09/103,873 : Examiner: J. Diaz
Filed: June 24, 1998 :
For: SEMICONDUCTOR DEVICE AND :
METHOD FOR FABRICATING THE SAME :

RECEIVED
6-26-01
JUL 15 2001
TECHNOLOGY CENTER 2800

AMENDMENT AND REQUEST FOR EXTENSION OF TIME

Assistant Commissioner for Patents
Washington, DC 20231

S I R :

Responsive to the Official Action dated January 30, 2001, please
amend the above-identified application as follows:

CLAIMS:

Please replace claim 1 with the following amended claim:

- 1 A semiconductor device, comprising:
2 a capacitor provided on a supporting substrate having an integrated
3 circuit thereon and including a lower electrode, a dielectric film, and an upper
4 electrode;
5 a first interlayer insulating film provided so as to directly cover the
6 capacitor;
7 a first interconnect selectively provided on the first interlayer
8 insulating film and electrically connected to the integrated circuit and the
9 capacitor through a first contact hole formed in the first interlayer insulating
10 film;
11 a second interlayer insulating film having a tensile stress provided
12 so as to directly cover the first interconnect and the first interlayer insulating
13 film;